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| *Перв. примен* | *ИУ4.11.03.03.23.05.52.09.001* | *Форма* | *Зона* | *Поз.* | | *Обозначение* | | | | *Наименование* | | | | | *Кол.* | *Примечание* | |
|  |  |  | |  | | | | *Документация* | | | | |  |  | |
|  |  |  | |  | | | |  | | | | |  |  | |
| *A1* |  |  | | *ИУ4.11.03.03.23.05.52.09.001 Э1* | | | | *Схема электрическая* | | | | | *1* |  | |
|  |  |  | |  | | | | *структурная* | | | | |  |  | |
| *А3* |  |  | | *ИУ4.11.03.03.23.05.52.09.001 Э3* | | | | *Схема электрическая* | | | | | *1* |  | |
| *Справ* |  |
|  |  |  | |  | | | | *принципиальная* | | | | |  |  | |
| *А4* |  |  | | *ИУ4.11.03.03.23.05.52.09.001 ПЭ 3* | | | | *Перечень элементов* | | | | | *1* |  | |
| *А3* |  |  | | *ИУ4.11.03.03.23.05.52.09.001 СБ* | | | | *Сборочный чертёж* | | | | | *1* |  | |
| *А3* |  |  | | *ИУ4.11.03.03.23.05.52.09.001 Э0* | | | | *Измерительный стенд* | | | | | *1* |  | |
|  |  |  | | *ИУ4.11.03.03.23.05.52.09.001 ПД1* | | | | *Сравнение моделирования* | | | | | *1* |  | |
|  |  |  | |  | | | | *и экспериментальных данных* | | | | |  |  | |
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|  | |  |  |  | |  | | | | *Детали* | | | | |  |  | |
| *А3* |  | *1* | | *ИУ4.11.03.03.23.05.52.09.002* | | | | *Плата печатная* | | | | | *1* |  | |
|  |  | *2* | |  | | | | *Радиатор 1* | | | | | *2* |  | |
| *Подп. и дата* |  |  |  | *3* | |  | | | | *Радиатор 2* | | | | | *1* |  | |
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| *Инв. N дубл.* |  |
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|  |  |  | |  | | | | *Конденсаторы* | | | | |  |  | |
|  |  | *4* | |  | | | | *Конденсатор электролитический* | | | | | *2* | *C1, C12* | |
| *Взам. инв. N* |  | *K50-35 220мкФ 100В (Jamicon, США)* | | | | |
|  |  | *5* | |  | | | | *Конденсатор плёночный* | | | | | *2* | *C2, C13* | |
| *CL21, 1мкФ 63В (Китай)* | | | | |
|  |  | *6* | |  | | | | *Конденсатор керамический К10-17Б* | | | | | *1* | *С3* | |
| *имп., 220нФ, 50В (Китай)* | | | | |
|  |  | *7* | |  | | | | *Конденсатор электролитический* | | | | | *1* | *С4* | |
| *Подп. и дата* |  | *220мкФ, 50В (EPCOS, Германия)* | | | | |
|  |  | *8* | |  | | | | *Конденсатор керамический К10-17Б* | | | | | *1* | *С5* | |
| *имп., 470нФ, 50В (Китай)* | | | | |
|  |  | |  | |  |  | *ИУ4.11.03.03.23.05.52.09.001* | | | | | | | | |
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| *Изм* | *nucm* | | *N докум.* | | *Подпись* | *Даmа* |
| *Инв. N подл.* |  | *Разраб.* | | | *Дорунц Ш.А.* | |  |  | *Усилитель низких частот*  *Спецификация* | | *Лит.* | | | *Лист* | | | *Листов* |
| *Пров.* | | | *Семенцов С.Г* | |  |  |  |  |  | *1* | | | *2* |
|  | | |  | |  |  | *МГТУ им. Н.Э. Баумана Кафедра ИУ4*  *Группа ИУ4-53Б* | | | | | | |
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|  |  | *9* | |  | | | | *Конденсатор электролитический* | *2* | *C6, С11* | |
| *K50-6, 10мкФ, 25В (Jamicon, США)* |
|  |  | *10* | |  | | | | *Конденсатор керамический К10-17Б* | *1* | *С7* | |
| *имп., 220пФ, 50В (Китай)* |
|  |  | *11* | |  | | | | *Конденсатор пленочный* | *1* | *С8* | |
| *CL21, 100пФ, 100В (Китай)* |
|  |  | *12* | |  | | | | *Конденсатор керамический К10-17Б* | *1* | *С9* | |
| *имп., 100пФ, 100В (Китай)* |
|  |  | *13* | |  | | | | *Конденсатор электролитический* | *1* | *С10* | |
| *K50-35, 470мкФ 10В (Jamicon, США)* |
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| *Справ* |  |
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|  |  |  | |  | | | | *Разъёмы* |  |  | |
| *Инв. N дубл.* |  |  |  | *16* | |  | | | | *Клеммник разъёмный 15EDGRC-*  *3.81-03P (Degson, Китай)* | *1* | *XS1* | |
|  |  | *17* | |  | | | | *Клеммник разъёмный 15EDGRC-*  *3.81-02P (Degson, Китай)* | *1* | *XS2* | |
|  |  | *18* | |  | | | | *Гнездо стерео 3.5мм ST-025* | *1* | *XS3* | |
|  |  |  | |  | | | | *(Dragon City Industries, Китай)* |  |  | |
| *Взам. инв. N* |  |
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| *Перв. примен* | ИУ4.11.03.03.23.05.52.09.001 | *Форма* | *Зона* | *Поз.* | | *Обозначение* | | | | *Наименование* | *Кол.* | *Примечание* | |
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|  |  |  | |  | | | | *Диоды* |  |  | |
|  |  | *4* | |  | | | | *1N4007* | *4* | *VD2, VD3,*  *VD4, VD5* | |
| *Справ* |  |
|  |  |  | |  | | | | *(Diotec Semiconductor, Германия)* |  |  | |
|  |  |  | |  | | | |  |  |  | |
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|  |  |  | |  | | | | *Резисторы* |  |  | |
|  |  | *19* | |  | | | | *CF-100 1Вт 2,2кОм 5%* | *1* | *R1* | |
|  |  | *20* | |  | | | | *CF-100 1Вт 1кОм 5%* | *2* | *R2, R3* | |
|  |  | *21* | |  | | | | *SQP 5Вт 0.22Ом 5%* | *2* | *R4, R6* | |
|  | |  |  | *22* | |  | | | | *CF-25 0,25Вт 2,7кОм 5%* | *1* | *R5* | |
|  |  | *23* | |  | | | | *CF-25 0,25Вт 8,2кОм 5%* | *1* | *R7* | |
|  |  | *24* | |  | | | | *CF-25 0,25Вт 22кОм 5%* | *1* | *R8* | |
| *Подп. и дата* |  |
|  |  | *25* | |  | | | | *MO-200 2Вт 1Ом 5%* | *1* | *R9* | |
|  |  | *26* | |  | | | | *SQP 10Вт 0.33Ом 5%* | *1* | *R10* | |
|  |  | *27* | |  | | | | *CF-25 0,25Вт 100Ом 5%* | *1* | *R11* | |
|  |  | *28* | |  | | | | *CF-25 0,25Вт 750Ом 5%* | *1* | *R12* | |
| *Инв. N дубл.* |  |  |  | *29* | |  | | | | *CF-25 0,25Вт 3Ом 5%* | *1* | *R13* | |
|  |  |  | |  | | | |  |  |  | |
|  |  |  | |  | | | | *Транзисторы* |  |  | |
|  |  | *30* | |  | | | | *TIP142 (STMicroelectronics, Франция)* | *1* | *VT1* | |
| *Взам. инв. N* |  |
|  |  | *31* | |  | | | | *BC556B* | *2* | *VT2, VT3* | |
|  |  | *32* | |  | | | | *(Diotec Semiconductor, Германия)* | *1* |  | |
|  |  | *33* | |  | | | | *TIP147 (STMicroelectronics, Франция)* | *1* | *VT4* | |
| *Подп. и дата* |  |
|  |  | *34* | |  | | | | *BD241C (STMicroelectronics, Франция)* | *1* | *VT5* | |
|  |  |  | |  | | | |  |  |  | |
| *Инв. N* |  |  |  |  | |  | | | |  |  |  | |
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